

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7993	257/239,261,295,298,314-326.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 07:35
L2	5435	438/201,211,216,241,257,258,260-266,591,593.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 07:36
L3	12497	1 OR 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 07:36
L4	841	3 AND (select\$3 near gate) WITH ((charg\$3 near storag\$3) ONO FG (float\$3 near gate) (oxide near nitride near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 07:41
L5	318	4 AND ((BL (bit NEAR line\$1)) WITH (word near line\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 07:42
L6	858	3 AND (SG (select\$3 near gate)) WITH ((charg\$3 near storag\$3) ONO FG (float\$3 near gate) (oxide near nitride near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 08:22
L7	324	6 AND ((BL (bit NEAR line\$1)) WITH (word near line\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 08:19
L8	11	("5280446" "5402371" "5408115" "5422504" "5455792" "5494838" "5969383" "6177318" "6248633" "6255166" "6587381").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/22 08:00
L9	458712	"257"/\$.ccls. OR "438"/\$.ccls. OR "365"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 08:19

L10	1290	9 AND ((SG SL (select\$3 near (gate line\$1))) WITH (between near2 (BL ((dop\$3 bit) NEAR line\$1))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 08:42
L11	546	10 AND ((charg\$3 near storag\$3) ONO FG (float\$3 near gate) (oxide near nitride near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:27
L12	179	11 AND (side adjacent next) NEAR (SG SL (select\$3 NEAR (line\$1 gate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 08:25
L13	43	("20020191453" "20030007387" "20030020123" "20030025149" "20030025150" "20030027411" "20030031064" "20030034530" "20030048674" "20030072191" "20030072194" "20030076717" "20030095443" "20030103388" "20030123303" "20030137875" "20030146450" "20030151070" "20030164517" "20030174558" "20030179609" "20030179621" "20030185054" "20030198102" "20030198103" "20040013018" "20040013027" "20040061139" "5408115" "5422504" "5494838" "5696383" "6177318" "6248633" "6255166" "6587380" "6587381" "6646916" "6650591" "6707695" "6707720" "6707742" "6735118").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/22 08:35
L14	297	(SG SGL (select\$3 near (gate line\$1))) NEAR2 between NEAR2 (BL ((dop\$3 bit) NEAR line\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:28
L15	305	(SG SGL (select\$3 near (gate line\$1))) NEAR2 between NEAR2 (BL ((dop\$3 bit diffus\$3 implant\$5) NEAR (region\$1 line\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:01
L16	10	15 AND ((charg\$3 near storag\$3) ONO FG (float\$3 near gate) (oxide near nitride near oxide)) WITH (side adjacent next) NEAR (SG SL (select\$3 NEAR (line\$1 gate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 08:58

L17	10	15 AND ((charg\$3 near storag\$3) ONO FG (float\$3 near gate) (oxide near nitride near oxide)) WITH (side adjacent next) NEAR (SG SGL (select\$3 NEAR (line\$1 gate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 08:49
L18	32630	(SG SGL (select\$3 near (gate line\$1))) AND (BL ((dop\$3 bit diffus\$3 implant\$5) NEAR (region\$1 line\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:20
L19	123	18 AND ((charg\$3 near storag\$3) ONO FG (float\$3 near gate) (oxide near nitride near oxide)) WITH (side adjacent next) NEAR (SG SGL (select\$3 NEAR (line\$1 gate)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:05
L20	78	15 AND ((charg\$3 near storag\$3) ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:04
L21	71	(SG SGL (select\$3 near (gate line\$1))) ADJ2 between ADJ2 (BL ((dop\$3 bit diffus\$3 implant\$5) NEAR (region\$1 line\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:02
L22	4155	18 AND ((charg\$3 near storag\$3) ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:04
L23	8894	18 AND ((charg\$3 near storag\$3) ONO FG (float\$3 near gate) (oxide near nitride near oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:06
L24	4721,	23 AND ((oxide insualt\$3 dielectric) NEAR (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:06
L25	5513	23 AND ((oxide insulat\$3 dielectric) NEAR (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:10

L26	3042	22 AND ((oxide insulat\$3 dielectric) NEAR (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:07
L27	963	26 AND ((non NEAR volatile) ADJ memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:11
L28	48	27 AND (((dual two) NEAR bit) ADJ memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:11
L29	72	26 AND (((dual two) NEAR bit) ADJ memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:11
L30	11	(SG SGL (select\$3 near (gate line\$1))) ADJ between ADJ (BL ((dop\$3 bit diffus\$3 implant\$5) NEAR (region\$1 line\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:27
L31	45	((charg\$3 near (trap\$4 storag\$3)) ONO (oxide near nitride near oxide)) WITH (BL ((dop\$3 diffus\$3 implant\$5 bit) NEAR line\$1)) WITH (select\$3 ADJ (gate line\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 09:37
L32	201	((charg\$3 near (trap\$4 storag\$3)) ONO (oxide near nitride near oxide)) SAME (BL ((dop\$3 diffus\$3 implant\$5 bit) NEAR line\$1)) SAME (select\$3 ADJ (gate line\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:08
L33	7	("5254217" "5279982" "5371030" "5397726" "5705419" "5918124" "6080624").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/22 09:51
L34	2249	((charg\$3 near (trap\$4 storag\$3)) ONO (oxide near nitride near oxide)) AND (BL ((dop\$3 diffus\$3 implant\$5 bit) NEAR line\$1)) AND (select\$3 ADJ (gate line\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:09

L35	2695	((charg\$3 near (trap\$4 storag\$3)) ONO (oxide near nitride near oxide)) AND (BL ((dop\$3 diffus\$3 implant\$5 bit) NEAR (region\$1 line\$1))) AND (select\$3 ADJ (gate line\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:10
L36	2338	35 AND substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:10
L37	2110	36 AND ((oxide insulat\$3 dielectric) NEAR (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:11
L38	2037	37 AND memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:11
L39	693	37 AND ((non NEAR volatile) ADJ memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:48
L40	542	39 AND ((source drain S/D) near (region\$1 area\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:14
L41	430	40 AND (word ADJ line\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/22 10:15
L42	10	((non NEAR volatile) ADJ memory) AND (BL (bit NEAR line\$1)) AND ((S/D (source drain) diffus\$3 implant\$5) NEAR region\$1) AND (plural\$3 NEAR select\$3 NEAR (gate line\$1)) AND (charge NEAR (trap\$4 storage)) AND (word ADJ line\$1).CLM.	US-PGPUB; USPAT	OR	ON	2005/07/22 10:55
L43	0	((non NEAR volatile) ADJ memory) AND (BL (bit NEAR line\$1)) AND ((S/D (source drain) diffus\$3 implant\$5) NEAR region\$1) AND (plural\$3 NEAR select\$3 NEAR (gate line\$1)) AND (charge NEAR (trap\$4 storage)) AND (word ADJ line\$1) AND ((dielectric oxide insulat\$3) NEAR (layer film))).CLM.	US-PGPUB; USPAT	OR	ON	2005/07/22 10:56